

Customer No.: 31561
Application No: 10/710,671
Docket No.:13085-US-PA

In the Specification:

Please amend paragraph 11 as follows:

Moreover, the read-out current of the memory is smaller due to a lot of memory cells are ~~serial~~ being serially connected in an array. This slows down the memory running speed and affects overall electrical performance of the memory cell.

Please amend paragraph 37 as follows:

The aforementioned memory cell row 132 includes the memory cell structures 103a ~ 103d formed by the gate structures 106a ~ 106d, the spacers 118 and the select gate structures 120a ~ 120d on the active region 104. Since there ~~is~~ are no gaps between the memory cells 130a ~ 130d, the integration density of the memory cell array is increased.